Prof. Ohmi's Paper

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E988(C) Tatsufumi Hamada, Yuji Saito, Masaki Hirayama, Sigitoshi Sugawa, Herzl Aharoni, and Tadahiro Ohmi, “(100) and (111) Si MOS Transistors Fabricated With Low Growth Temperature (400 °C) Gate Oxide by Kr/O2 Microwave-Excited High-Density Plasma,” IEEE Transactions on Semiconductor Manufacturing, Vol. 14, No. 4, pp. 418-420, November 2001.

